

View Online at <https://aerobasegroup.com/nsn/5961-01-624-7502>

**Inclosure Material:**

Glass and metal

**Overall Length:**

Between 1.335 inches and 1.345 inches

**Overall Height:**

Between 0.147 inches and 0.200 inches

**Overall Width:**

Between 0.535 inches and 0.545 inches

**Function For Which Designed:**

Programmable transistor

**Internal Configuration:**

Field effect

**Electrode Internally-electrically Connected To Case:**

Gate

**Internal Junction Configuration:**

Npn

**Voltage Rating In Volts Per Characteristic:**

-0.5 drain to source voltage and 65.0 drain to source voltage

**Current Rating Per Characteristic:**

10.0 microamperes zero-gate-voltage drain current

**Power Rating Per Characteristic:**

90.0 watts cw power

**Maximum Operating Temperature Per Measurement Point:**

150.0 degrees celsius case and 200.0 degrees celsius junction

**Product Name:**

Rf power field effect transistor

**Special Features:**

Tech data shows this item was no longer manufactured since 2010; in tape and reel, r3 suffix =250 units per 56mm, 13 inch reel; rohs compliant; designed for gsm and gsm edge base station applications with frequencies from 1800 to 2000 mhz; designed for maximum gain and insertion phase flatness; suitable for fm, tdma, cdma and multicarrier amplifier applications; to be used in class ab for gsm and gsm edge cellular radio applications; integrated esd protections; high efficiency; high linearity

**Terminal Type And Quantity:**

3 pin

**Shelf Life:**

N/a

**Unit Of Measure:**

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**Demilitarization:**

No

**Fiig:**

A110a0